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| Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary) | | | Complete If Known | | |
| | | | Application Number | 10/075,390 | |
| | | | Filing Date | February 15, 2002 | |
| | | | First Named Inventor | Kristy A. Campbell | |
| | | | Art Unit | 2818 | |
| | | | Examiner Name | Not Yet Assigned | |
| Sheet | 1 | of | 1 | Attorney Docket Number | M4065.0505/P505 |

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¹ Applicant's unique citation designation number (optional). ² See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that Issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

| OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS | | | |
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| Examiner Initials* | Cite No. ¹ | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published. | T ² |
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| | | Filing Date | February 15, 2002 |
| | | First Named Inventor | Kristy A. Campbell |
| | | Group Art Unit | 2818 |
| | | Examiner Name | Not Yet Assigned |
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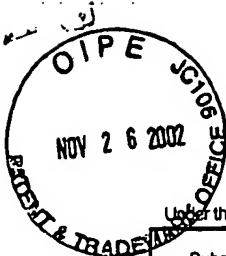
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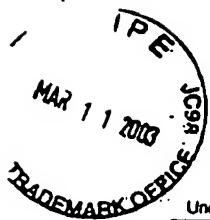
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| | | | | Filing Date | February 15, 2002 |
| | | | | First Named Inventor | Kristy A. Campbell |
| | | | | Art Unit | 2818 |
| | | | | Examiner Name | Not Yet Assigned |
| Sheet | 2 | of | 4 | Attorney Docket Number | M4065.0505/P505 |

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| | | | | Filing Date | July 10, 2002 |
| | | | | First Named Inventor | Kristy A. Campbell |
| | | | | Group Art Unit | 2818 |
| | | | | Examiner Name | Not Yet Assigned |
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